EDITORIAL

Greetings from the new Editor-in-Chief

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Greetings from the new Editor-in-Chief

On 1 January 2012 I will be assuming the position of Editor-in-Chief of the journal *Semiconductor Science and Technology* (SST). I am flattered by the confidence expressed in my ability to carry out this challenging job and I will try hard to justify this confidence.

The previous Editor-in-Chief, Laurens Molenkamp, University of Würzburg, Germany, has worked tirelessly for the last ten years and has done an excellent job for the journal. Everyone at the journal is profoundly grateful for his leadership and for his achievements.

In 2012 several new members will join the Editorial Board: Professor Deli Wang (University of California, San Diego) with considerable expertise in semiconductor nanowires, Professor Saskia Fischer (Humboldt University, Berlin, Germany) with a background in semiconductor quantum devices, and Professor Erwin Kessels (Eindhoven University of Technology, Netherlands) with extensive experience in plasma processing of thin films and gate oxides. In particular, I want to express my gratitude to Professor Israel Bar-Joseph (Weizmann Institute of Science, Israel) and Professor Maria Tamargo (The City College of New York, USA), who will leave next year and who have vigorously served the Editorial Board for years.

The journal has recently introduced a fast-track option for manuscripts. This option is a high-quality, high-profile outlet for new and important research across all areas of semiconductor research. Authors can expect to receive referee reports in less than 20 days from submission. Once accepted, you can expect the articles to be online within two or three weeks from acceptance and to be published in print in less than a month. Furthermore, all fast-track communications published in 2011 will be free to read for ten years. More detailed information on fast-track publication can be found on the following webpage:

http://iopscience.iop.org/0268-1242/page/Fast track communications

It is encouraging to see that since the journal introduced pre-review, with the aim to raise the quality of our content, three years later the number of published articles has remained stable at around 220 per year, whilst the number of downloads and citations to the journal has grown.

In 2011, three topical issues have been published, on:

- (Nano)characterization of semiconductor materials and structures (Guest Editor: Alberta Bonanni, University of Linz, Austria)
- Flexible OLEDs and organic electronics (Guest Editors: Jang-Joo Kim, Min-Koo Han, Cambridge University, UK, and Yong-Young Noh, Seoul National University, Korea)
- From heterostructures to nanostructures: an 80th birthday tribute to Zhores Alferov (Guest Editor: Dieter Bimberg, Technische Universität Berlin, Germany)

For the coming years, I will strongly support that the number of published topical issues will continue on the same level or slightly rise. SST has planned the publication of the following topical issues for 2012:

- Non-polar and semipolar nitride semiconductors (Guest Editors: Jung Han, Yale University, USA, and Michael Kneissl, Technische Universität Berlin, Germany)
- Topological insulators (Guest Editors: Alberto Morpurgo, Université de Genève, Switzerland and Björn Trauzettel, Universität Basel, Switzerland)
- Atomic layer deposition (Guest Editor: Marek Godlewski, Polish Academy of Sciences, Poland)
- 50th Anniversary of the laser diode (Guest Editors: Mike Adams, Univeristy of Essex, UK and Stephane Calvez, University of Strathclyde, UK)

In addition to the traditional topics of SST, I as Editor-in-chief, strongly support and welcome the submission of manuscripts on organic semiconductors, topological insulators, semiconductor nanostructures for photovoltaic, solid-state lighting and energy harvesting, IC application beyond Moore’s law and fundamental works on semiconductors based on abundant materials. I am extremely optimistic about the future of SST. I believe that we will raise the standards of acceptance while maintaining the short time from submission to first decision. I am confident that we will continue to improve the quality of the papers published in this already first-class journal. I look forward to working with the journal’s excellent staff and Editorial Board Members.